

## Features

- Frequency: 15GHz~17GHz
- Small Signal Gain: 20dB
- Output P<sub>-1dB</sub>: 38dBm
- PAE:30%@P<sub>-1dB</sub>, f=16GHz
- IM<sub>3</sub>: -23dBc, 29dBm/Tone@15.5GHz
- Die size: 4.1mm×4.5mm×0.1mm
- Supply Voltage: +7V/-V<sub>G</sub>
- Packaged: Bare Die

## Typical Applications

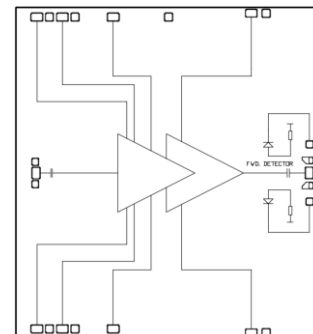
- Point-to-Point Radios
- SATCOM
- Military and Space
- Radar

## General Description

SAC3152 is a Ku-band GaAs MMIC power amplifier. SAC3152 provides 20 dB of gain, and 38dBm of output power for 1 dB compression and 30% PAE from +7V supply.

The chip has surface passivation for protection and backside via holes and gold metallization to allow a conductive epoxy die attach process.

## Functional Diagram



## Electrical Performance

T<sub>A</sub>=25°C, V<sub>D</sub>=+7V, I<sub>DQ</sub>=2A, Z<sub>0</sub>=50Ω, CW

Parameter	Min.	Typ.	Max.	Units
Frequency Range	15	—	17	GHz
Small Signal Gain	16	20	—	dB
Small Signal Gain Flatness	—	±1.5	—	dB
Reverse Isolation	—	-60	—	dB
RF Input VSWR	—	1.8	—	:1
Output P <sub>-1dB</sub>	37	38	—	dBm
Drain Voltage (V <sub>D</sub> )	7	—	8	V
Gate Current	—	2	24	mA
Supply Current (I <sub>D</sub> )***	—	—	5	A
Thermal Resistance**	—	3	—	°C/W

\*\* Measurement taken at P<sub>out</sub> = OP<sub>-1dB</sub>, IR method. 100% DC power is dissipated on the device the thermal resistance is 3.3°C/W

\*\*\* Adjust V<sub>G</sub> between -1.5V to -0.4V to achieve I<sub>DQ</sub>= 2A , and typical V<sub>G</sub> voltage is -0.8V.

## Absolute Maximum Ratings

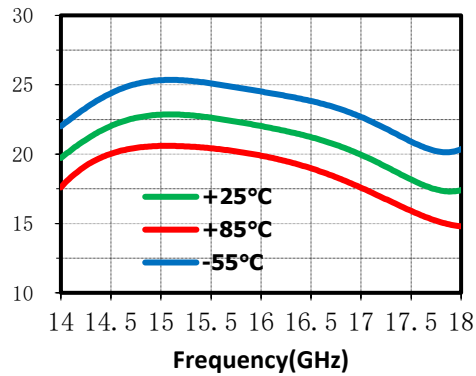
Maximum Input Power	+23dBm	Operating Temperature (Backside)	-55°C~+85°C
Channel Temperature	150°C	Storage Temperature	-55°C~+150°C
Maximum V <sub>D</sub>	+8.5V	V <sub>G</sub> Range	-3V~-0.4V

## Typical Performance Curve

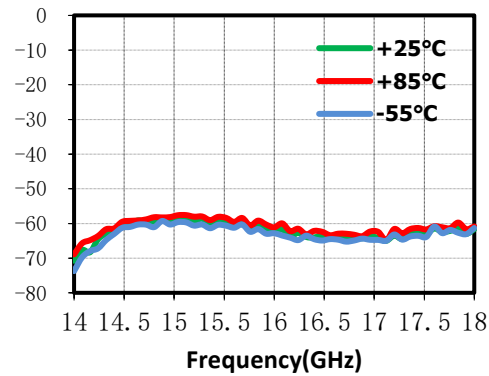
The following data are obtained by SAC3152 evaluation board

$V_D = +7V$ ,  $I_{DQ} = 2A$ , CW,  $T_A = +25^\circ C$

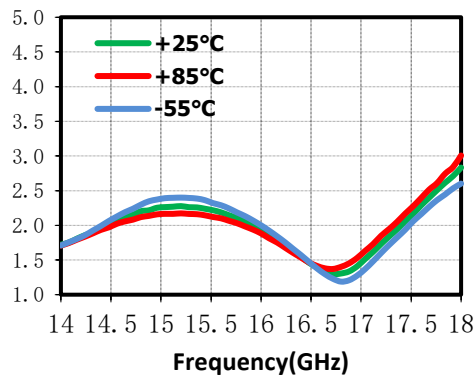
Small Signal Gain(dB) vs. Temperature



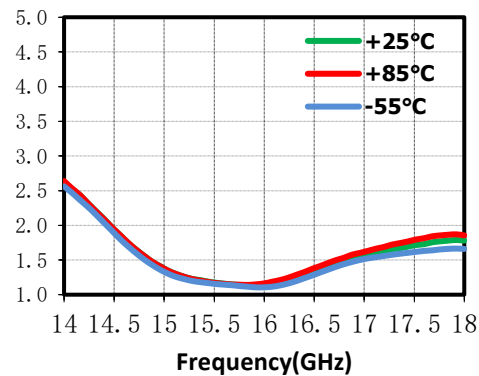
Isolation(dB) vs. Temperature



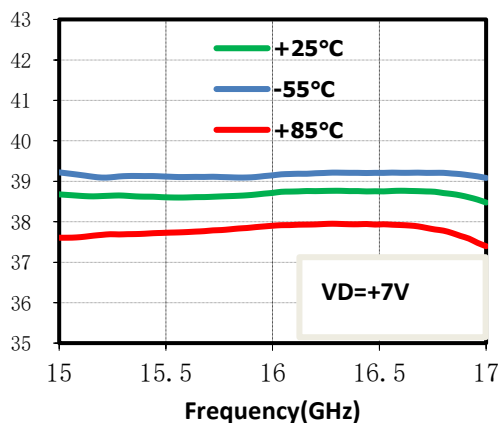
RF Input VSWR (:1) vs. Temperature



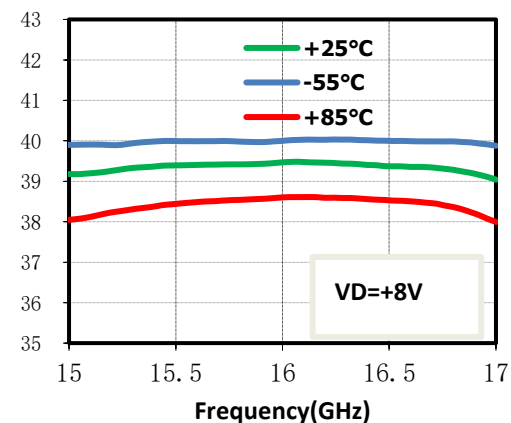
RF Output VSWR(:1) vs. Temperature



Output P<sub>1dB</sub>(dBm) vs. Temperature



Output P<sub>1dB</sub>(dBm) vs. Frequency



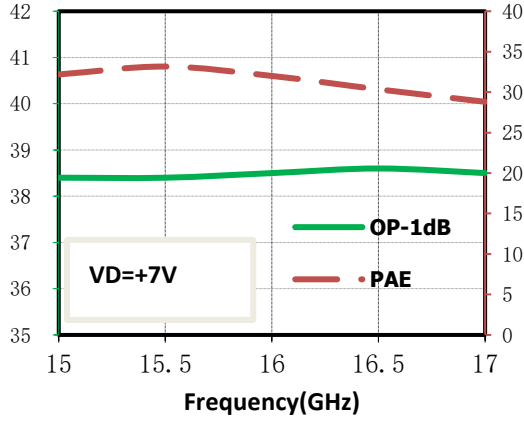
# SAC3152



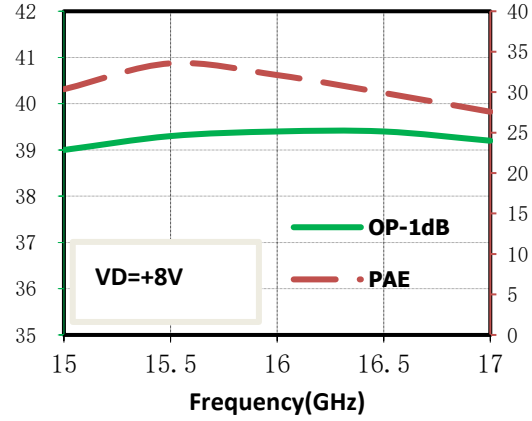
GaAs MMIC Power Amplifier  
15GHz~17GHz 38dBm

Rev

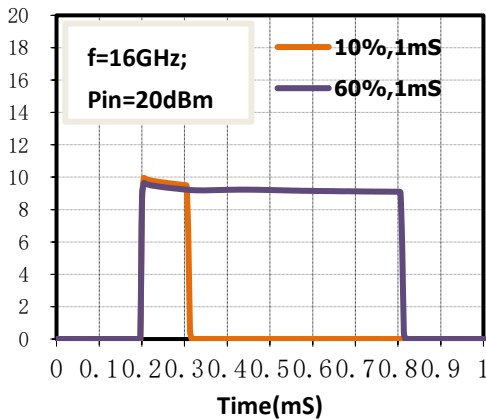
OP<sub>-1</sub>dB(dBm),PAE(%) vs. Frequency



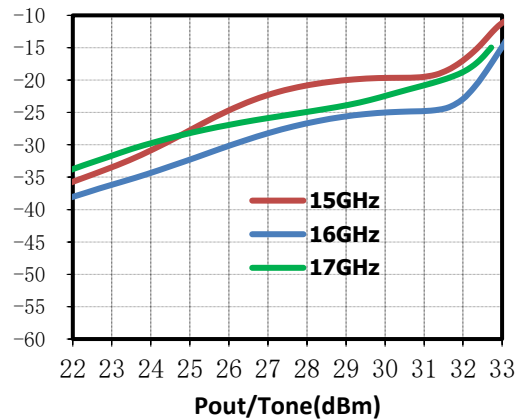
OP<sub>-1</sub>dB(dBm),PAE(%) vs. Frequency



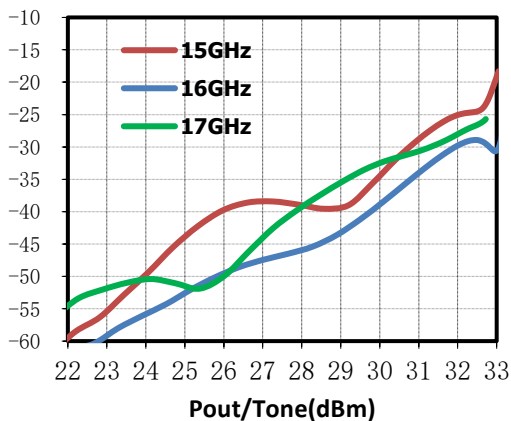
Output Power(W)vs. VD, Pulse width



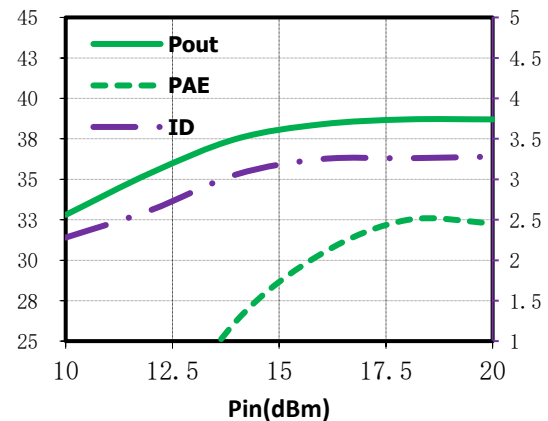
IM<sub>3</sub>(dBc)vs. Pout/Tone



IM<sub>5</sub>(dBc)vs. Pout/Tone



Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=15GHz



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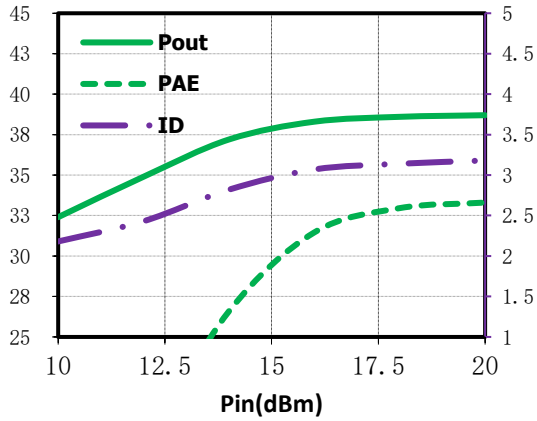
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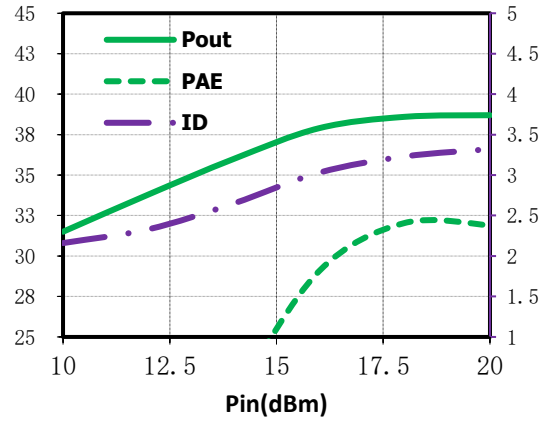
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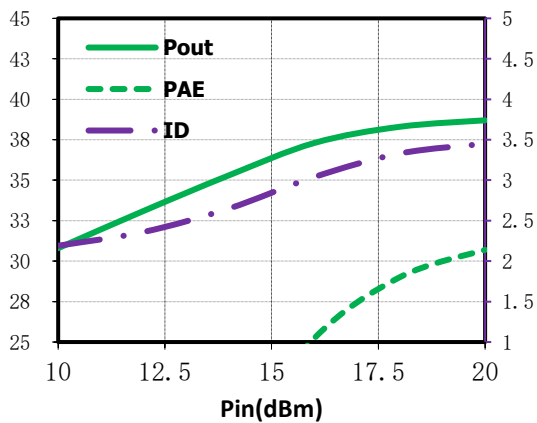
Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=15.5GHz



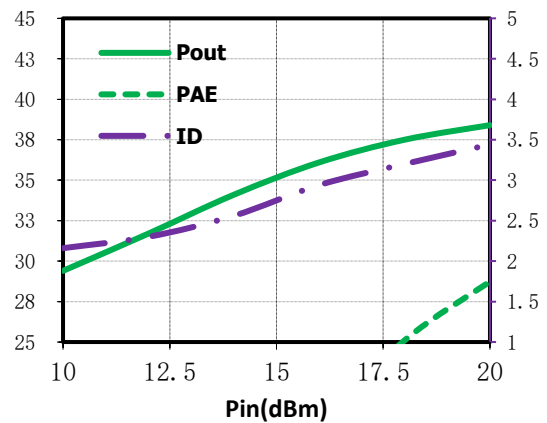
Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=16GHz



Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=16.5GHz



Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=17GHz



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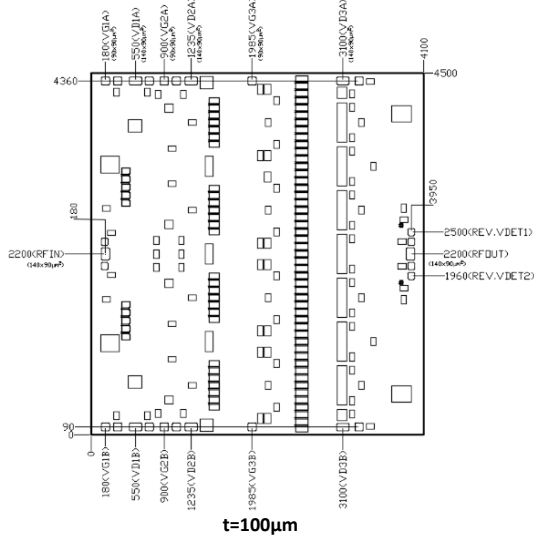
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15GHz~17GHz 38dBm

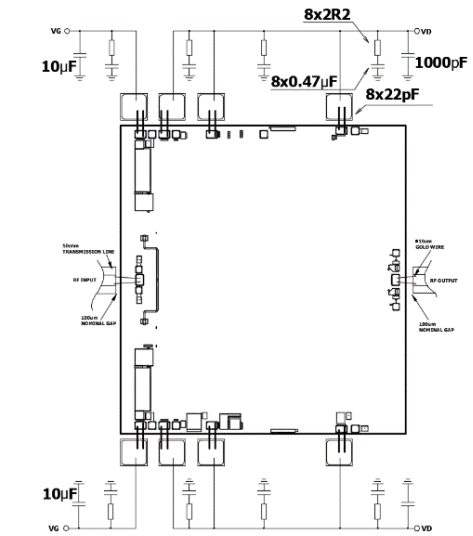
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## Die Outline

(All dimensions in  $\mu\text{m}$ )



## Assembly Diagram



VDx and VGx need to be fed simultaneously on both sides

## Attention:

1. SAC3152 requires drain positive voltage (VDx) and gate negative voltage (VGx) bias, which shall be applied before applying drain positive voltage. Ensure that the gate negative voltage is applied;
2. Vacuum AuSn eutectic soldering is recommended;
3. The single-layer decoupling capacitor shall be of small volume and thin dielectric type as far as possible;
4. When using drain pulse voltage modulation, ensure that the maximum overshoot voltage does not exceed 8.5V.

## Revision History

Revision	Date	Comment
1.0	December 1, 2022	First Release